Electronic Supplementary Information

White OLEDs Based on a Novel Eu^{III}–Tetrakis– β –Diketonate Doped into 4,4'-*N*,*N*'-Dicarbazolebiphenyl as Emitting Material[†]

Silvanose Biju, Liang-Jin Xu, Cheng-Zhe Sun and Zhong-Ning Chen*

State Key Laboratory of Structural Chemistry, Fujian Institute of Research on the Structure of Matter, Chinese Academy of Science, Fuzhou, Fujian 35002, People's Republic of China

10% NBu ₄ [EuL ₄]					
Voltage	Х	у	Colour		
6V	0.612	0.322	Red		
7V	0.598	0.313	Red		
8V	0.394	0.342	White		
9V	0.337	0.321	White		
10V	0.302	0.297	White		
11V	0.295	0.274	White		
12V	0.274	0.270	White		
13V	0.261	0.272	White		

Table S1. CIE coordinates and emission colours of the devices ITO/PEDOT: PSS (50 nm)/NBu4 [EuL4] (10% or 20%): CBP (63% or 56%)-OXD7 (27% or 24%) (50 nm)/TPBI (50 nm)/LiF (1.5 nm)/Al (120 nm) at different voltages.

20% NBu₄ [EuL₄]

6V	0.617	0.311	Red	
7V	0.576	0.300	Red	
8V	0.339	0.328	White	
9V	0.328	0.282	White	
10V	0.302	0.272	White	
11V	0.295	0.274	White	
12V	0.279	0.263	White	
13V	0.262	0.260	White	



Fig. S1 ¹H NMR Spectrum of HL in CDCl₃



Fig. S2 ¹³C NMR Spectrum of HL in CDCl₃.





Fig. S3 ¹H NMR Spectrum of NBu₄[LaL₄] in CDCl₃⁻







Fig. S4 Low and high resolution ESI mass specta of NBu₄[LaL₄] with isotopic patters.





Fig. S5 Low and high resolution ESI mass spectra of NBu₄[EuL₄] with isotopic patters.



Fig. S6 Thermogravimetric curves of La^{III} and Eu^{III} complexes.



Fig. S7 ⁵D₀decay profile of NBu₄[EuL₄] at 298 K in solid state (λ_{ex} = 400 nm), monitored at 612 nm.



Fig. S8 Plot of cyclic voltammogram and HOMO, LUMO values of NBu₄[EuL₄].



Fig. S9 Electroluminescence spectra of the device ITO/PEDOT : PSS (50 nm) / NBu₄[EuL₄] (30%): CBP (49%)-OXD7 (21%) (50 nm)/TPBI (50 nm)/LiF (1.5 nm)/Al (120 nm) at different voltages.



Fig. S10 Electroluminescence spectra of the device ITO/PEDOT: PSS (50 nm)/ NBu₄ [EuL₄] (50%): CBP (35%)-OXD7 (15%) (50 nm)/TPBI (50 nm)/LiF (1.5 nm)/Al (120 nm) at different voltages.



Fig. S11 Electroluminescence spectra of the device ITO/PEDOT: PSS (50 nm)/NBu₄[EuL₄] (50 nm)/TPBI(50 nm)/LiF(1.5 nm)/Al(120 nm) diode at different voltages.



Fig. S12 Voltage (*V*)–Current density (*J*) characteristics of the device ITO/PEDOT: PSS(50nm)/ NBu₄ [EuL₄] (10-20%): CBP (70%) - OXD7 (30%) (50 nm)/TPBI (50 nm)/LiF (1.5 nm)/Al (120 nm).



Fig. S13 Current density (*J*) versus power efficiency (η_c) of the devices ITO/PEDOT: PSS(50 nm)/NBu₄[EuL₄] : CBP-OXD7 (50 nm)/TPBI (50 nm)/LiF (1.5 nm)/Al (120 nm) with the doping percentage of Eu complex being 10%, 20%, 30%, 50%, and 100%, respectively. The weight ratio of mixed host CBP : OXD7 is 7 : 3.